

# Power Transistor (400V, 0.1A)

## 2SC4505

### ●Features

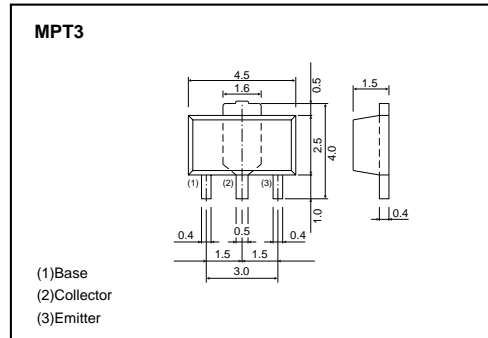
- 1) High breakdown voltage. ( $BV_{CEO} = 400V$ )
- 2) Low saturation voltage,  
typically  $V_{CE(sat)} = 0.05V$  at  $I_C / I_B = 10mA / 1mA$ .
- 3) High switching speed, typically  $t_f = 1.7\mu s$  at  $I_C = 100mA$ .
- 4) Complements the 2SC4505 and the 2SA1759.

### ●Packaging specifications and $h_{FE}$

|                              |         |
|------------------------------|---------|
| Type                         | 2SC4505 |
| Package                      | MPT3    |
| $h_{FE}$                     | PQ      |
| Marking                      | CE*     |
| Code                         | T100    |
| Basic ordering unit (pieces) | 1000    |

\* Denotes  $h_{FE}$

### ●Dimensions (Unit : mm)



### ●Absolute maximum ratings ( $T_a = 25^\circ C$ )

| Parameter                   | Symbol    | Limits      | Unit         |
|-----------------------------|-----------|-------------|--------------|
| Collector-base voltage      | $V_{CBO}$ | 400         | V            |
| Collector-emitter voltage   | $V_{CEO}$ | 400         | V            |
| Emitter-base voltage        | $V_{EBO}$ | 7           | V            |
| Collector current           | $I_C$     | 0.1         | A (DC)       |
|                             |           | 0.2         | A (Pulse) *1 |
| Collector power dissipation | $P_C$     | 0.5         | W            |
|                             |           | 2           | W *2         |
| Junction temperature        | $T_J$     | 150         | $^\circ C$   |
| Storage temperature         | $T_{stg}$ | -55 to +150 | $^\circ C$   |

\*1 Single pulse,  $P_w = 20ms$ , Duty = 1/2

\*2 When mounted on a 40×40×0.7mm ceramic board.

### ●Electrical characteristics ( $T_a = 25^\circ C$ )

| Parameter                            | Symbol        | Min. | Typ. | Max. | Unit    | Conditions                                   |
|--------------------------------------|---------------|------|------|------|---------|--|
| Collector-base breakdown voltage     | $BV_{CBO}$    | 400  | —    | —    | V       | $I_C = 50\mu A$                              |
| Collector-emitter breakdown voltage  | $BV_{CEO}$    | 400  | —    | —    | V       | $I_C = 1mA$                                  |
| Emitter-base breakdown voltage       | $BV_{EBO}$    | 7    | —    | —    | V       | $I_E = 50\mu A$                              |
| Collector cutoff current             | $I_{CBO}$     | —    | —    | 10   | $\mu A$ | $V_{CB} = 400V$                              |
| Emitter cutoff current               | $I_{EBO}$     | —    | —    | 10   | $\mu A$ | $V_{EB} = 6V$                                |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | —    | 0.05 | 0.5  | V       | $I_C / I_B = 10mA / 1mA$                     |
| Base-emitter saturation voltage      | $V_{BE(sat)}$ | —    | —    | 1.5  | V       | $I_C / I_B = 10mA / 1mA$                     |
| DC current transfer ratio            | $h_{FE}$      | 82   | —    | 270  | —       | $V_{CE} = 10V$ , $I_C = 10mA$                |
| Transition frequency                 | $f_T$         | —    | 20   | —    | MHz     | $V_{CE} = 10V$ , $I_E = -10mA$ , $f = 10MHz$ |
| Output capacitance                   | $C_{ob}$      | —    | 7    | —    | pF      | $V_{CB} = 10V$ , $I_E = 0A$ , $f = 1MHz$     |
| Turn-on time                         | $t_{on}$      | —    | 1    | —    | $\mu s$ | $I_C = -100mA$ , $R_L = 1.5k\Omega$          |
| Storage time                         | $t_{stg}$     | —    | 5.5  | —    | $\mu s$ | $I_{B1} = -I_{B2} = 10mA$                    |
| Fall time                            | $t_f$         | —    | 1.7  | —    | $\mu s$ | $V_{CC} = -150V$                             |

Transistors

●Electrical characteristics (Ta=25°C)

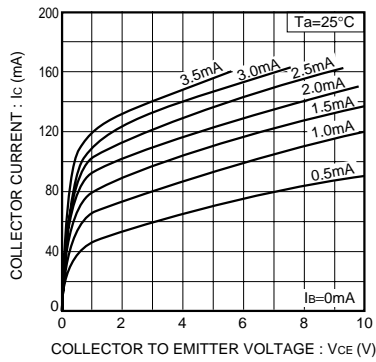


Fig.1 Ground emitter output characteristics

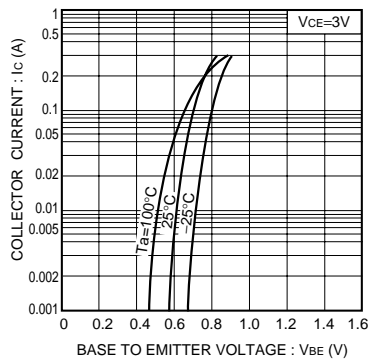


Fig.2 Ground emitter propagation characteristics

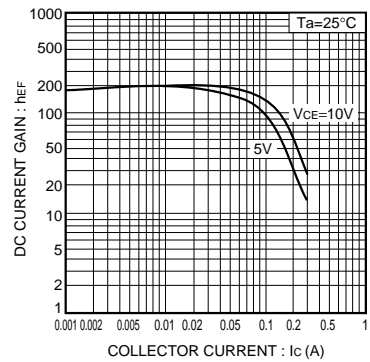


Fig.3 DC current gain vs. collector current ( I )

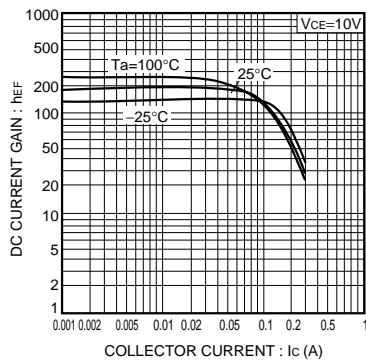


Fig.4 DC current gain vs. collector current ( II )

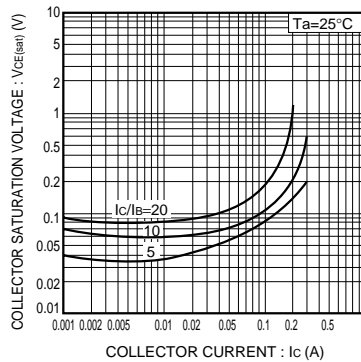


Fig.5 Collector-emitter saturation voltage vs. collector current

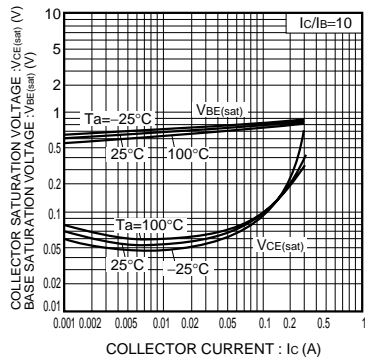


Fig.6 Collector-emitter saturation voltage vs. collector current  
Collector-base saturation voltage

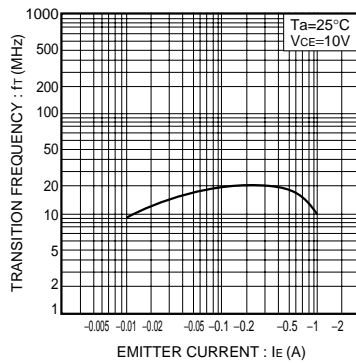


Fig.7 Gain bandwidth product vs. emitter current

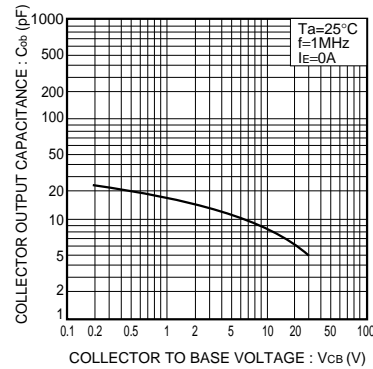


Fig.8 Collector output capacitance vs. collector-base voltage

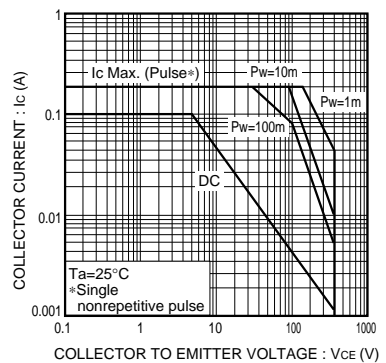


Fig.9 Safe operating area

## Transistors

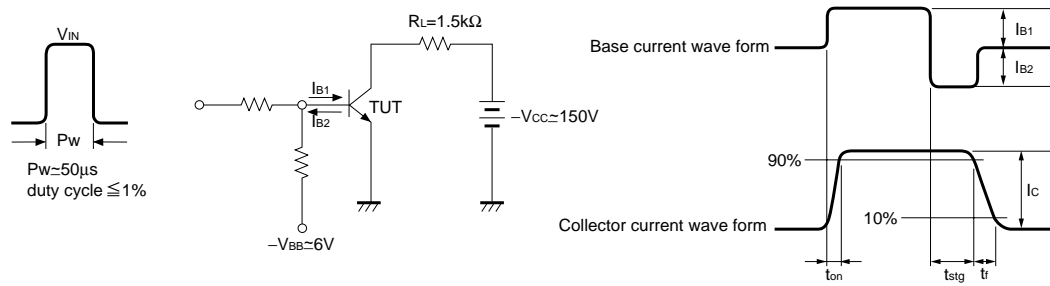


Fig.10 Switching time measurement circuit

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